TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74HCT573AP,TC74HCT573AF

### Octal D-Type Latch with 3-State Output

The TC74HCT573A is a high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Its inputs are compatible with TTL, NMOS, and CMOS output voltage levels.

Its 8-bit D-type latch is controlled by a latch enable input (LE) and an output enable input ( $\overline{OE}$ ).

When the  $\overline{\mbox{OE}}$  input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

### **Features**

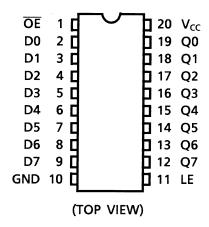
- High speed:  $t_{pd} = 18 \text{ ns}$  (typ.) at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $I_{CC} = 4 \mu A \text{ (max)}$  at  $T_a = 25 \text{°C}$
- Compatible with TTL outputs:  $V_{IL}$  = 0.8 V (max)  $V_{IH}$  = 2.0 V (min)
- Output drive capability: 15 LSTTL loads
- Symmetrical output impedance:  $|I_{OH}| = I_{OL} = 6 \text{ mA (min)}$
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Pin and function compatible with 74LS573

# DIP20-P-300-2.54A TC74HCT573AF SOP20-P-300-1.27A

Weight

DIP20-P-300-2.54A : 1.30 g (typ.) SOP20-P-300-1.27A : 0.22 g (typ.)

# **Pin Assignment**



# **IEC Logic Symbol**

OE (1) LE (11)	EN C1	
D0 (2) (3) D1 (4) D2 (5) D3 (6) D4 (7) D5 (8) D6 (9)	1D ▷ ∇	(19) Q0 (18) Q1 (17) Q2 (16) Q3 (15) Q4 (14) Q5 (13) Q6 (12) Q7

# **Truth Table**

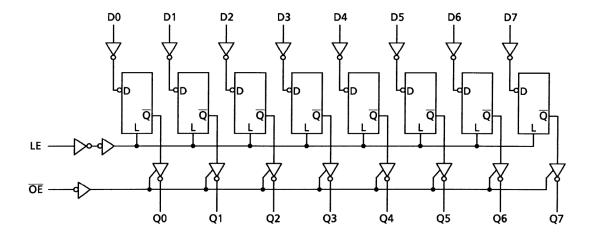
	Output		
ŌĒ	LE	D	Q
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

 $\mathsf{Q}_{\mathsf{n}} . \; \mathsf{Q}$  outputs are latched at the time when the LE input is taken to a low logic level.

# **System Diagram**



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### **Absolute Maximum Ratings (Note 1)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7	V
DC input voltage	V <sub>IN</sub>	-0.5~V <sub>CC</sub> + 0.5	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	l <sub>IK</sub>	±20	mA
Output diode current	lok	±20	mA
DC output current	lout	±35	mA
DC V <sub>CC</sub> /ground current	Icc	±75	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T <sub>stg</sub>	−65 <b>~</b> 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta =  $-40 \text{ to } 65^{\circ}\text{C}$ . From Ta =  $65 \text{ to } 85^{\circ}\text{C}$  a derating factor of  $-10 \text{ mW}/^{\circ}\text{C}$  shall be applied until 300 mW.

### **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	4.5~5.5	V
Input voltage	V <sub>IN</sub>	0~V <sub>CC</sub>	V
Output voltage	Vout	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	t <sub>r</sub> , t <sub>f</sub>	0~500	ns

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

### **Electrical Characteristics**

### **DC Characteristics**

Characteristics	Symbol	Test Condition		Ta = 25°C				Ta = -4	Unit	
Ondidotenstics Symbol		V(		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
High-level input voltage	V <sub>IH</sub>	_		4.5~5.5	2.0	_		2.0		V
Low-level input voltage	V <sub>IL</sub>	_		4.5~5.5		_	0.8	_	0.8	٧
High-level output	V <sub>OH</sub>	V <sub>IN</sub>	$I_{OH} = -20 \mu A$	4.5	4.4	4.5		4.4		V
voltage	VOH	$= V_{IH} \text{ or } V_{IL}$	$I_{OH} = -6 \text{ mA}$	4.5	4.18	4.31		4.13		٧
Low-level output	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OL} = 20 \mu A$	4.5		0.0	0.1	_	0.1	<b>V</b>
voltage	VOL		$I_{OL} = 6 \text{ mA}$	4.5	_	0.17	0.26		0.33	V
3-state output off-state current	loz	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = V <sub>CC</sub> or GND		5.5	l	_	±0.5	_	±5.0	μΑ
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	±0.1	_	±1.0	μΑ
Outcoont cumply		V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5			4.0	_	40.0	μΑ
Quiescent supply current	IC	Per input: V <sub>IN</sub> = 0.5 V or 2.4 V Other input: V <sub>CC</sub> or GND		5.5		_	2.0	_	2.9	mA

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### Timing Requirements (input: tr = tf = 6 ns)

Characteristics	Symbol	Test Condition	Ta = 25°C		Ta = -40 ~85°C	Unit	
			V <sub>CC</sub> (V)	Тур.	Limit	Limit	
Minimum pulse width	4		4.5	_	15	19	20
(LE)	t <sub>W (H)</sub>	_	5.5	_	14	17	ns
Minimum set-up time			4.5	_	10	13	
(data)	t <sub>S</sub>	_	5.5	_	9	11	ns
Minimum hold time	4.		4.5	_	5	5	20
(data)	t <sub>h</sub>	_	5.5	_	5	5	ns

### AC Characteristics (input: $t_r = t_f = 6$ ns)

Characteristics	Cumbal	Test Co	ondition		Ta = 25°C			Ta = -40~85°C		Unit	
Characteristics	Symbol		CL (pF)	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic	
0 1 11 11 11	t <sub>TLH</sub>		50	4.5	_	7	12	_	15	ns	
Output transition time	t <sub>THL</sub>		50	5.5		6	11	_	14	115	
			50	4.5	_	19	29	_	36		
Propagation delay time	t <sub>pLH</sub>		50	5.5		17	26	_	33	ns	
(LE-Q)	$t_{pHL}$		150	4.5	_	24	37	_	46	113	
` '			150	5.5		22	34	_	43		
			50	4.5	_	17	26	_	33		
Propagation delay time	t <sub>pLH</sub>		50	5.5		14	23	_	29	ns	
(D-Q)	$t_{pHL}$		150	4.5	_	22	34	_	43	113	
, ,				150	5.5		20	31	_	39	
		$R_L = 1 \text{ k}\Omega$	50	4.5		18	27	_	34		
Output enable time	$t_{pZL}$			5.5	_	15	24	_	30	ns	
Output chable time	t <sub>pZH</sub>		150	4.5	_	23	35	_	44		
			150	5.5		20	32	_	40		
Output disable time	$t_{pLZ}$	$R_L = 1 k\Omega$	50	4.5		18	24	_	30	ns	
Output disable time	t <sub>pHZ</sub>	N 1 K22	50	5.5		16	22	_	28	115	
Input capacitance	C <sub>IN</sub>	_	_			5	10	_	10	pF	
Output capacitance	C <sub>OUT</sub>	_	-			10	_	_		pF	
Power dissipation	C <sub>PD</sub>					38				pF	
capacitance	(Note)					30				рг	

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

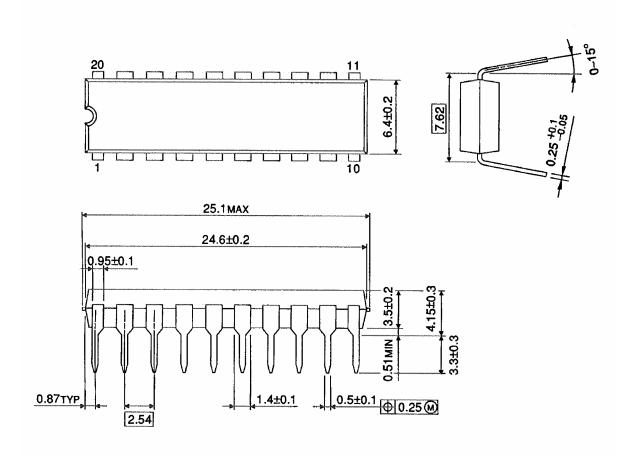
$$I_{CC}$$
 (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

And the total C<sub>PD</sub> when n pcs. of latch operate can be gained by the following equation:

$$C_{PD}$$
 (total) = 25 + 13 · n

# **Package Dimensions**

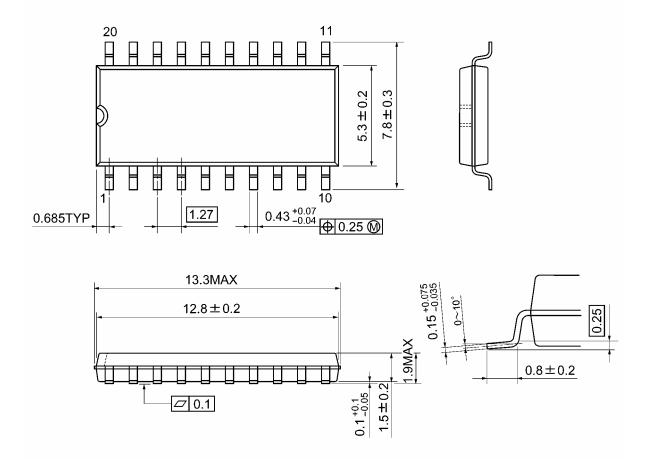




Weight: 1.30 g (typ.)

# **Package Dimensions**

SOP20-P-300-1.27A Unit: mm



Weight: 0.22 g (typ.)

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20070701-EN GENERAL

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